IFW/2826



Docket No.: 3449-0570PUS1 (PATENT)

In re Patent Application of:

Suk-Hun LEE

Application No.: 10/564,404

Filed: January 13, 2006

For: NITRIDE SEMICONDUCTOR LIGHT

EMITTING DEVICE

Confirmation No.: 1794

Art Unit: 2826

Examiner: Wilson, S.R.

LETTER

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Further to the Information Disclosure Statement filed on February 1, 2007, in the above-identified application, attached is a copied translation of an Office Action dated June 8, 2007, in the corresponding Chinese application. It will be noted from the Chinese Office Action that one (1) of the documents cited in the February 1, 2007, Information Disclosure Statement, i.e., KR-2002-0079659-A, was also cited in the Chinese Office Action.

Should there be any outstanding matters that need to be resolved in the present application, the Examiner is respectfully requested to contact James T. Eller, Jr., Reg. No. 39,538 at the telephone number of the undersigned below, to conduct an interview in an effort to expedite prosecution in connection with the present application.

Application No.: 10/564,404 Docket No.: 3449-0570PUS1

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. §§ 1.16 or 1.17; particularly, extension of time fees.

Dated: August 30, 2007

Respectfully submitted,

James T. Eller, Jr.

Registration No.: 39,538

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Our Ref: IP051531P

STATE INTELLECTUAL PROPERTY OFFICE OF PEOPLE'S REPUBLIC OF CHINA

Application No.:	2004800159493 Date of Notification:		
Attorney:	Jinwei GU, Jifu LIU Ju	ine 8, 2007	PATEN
Applicant:	G INNOTEK CO., LTD.		
Title of the Invention:	le of the Invention: NITRIDE SEMICONCUCTOR LIGHT EMITTING DEVICE		

Notification of the First Office Action (National Phase of PCT Application)

				(National Phase	of PCT Application)	
1. <u>[</u>	_ 1	invention und referred to as The State Intelle	ler Article 3 "the Patent ectual Prop	35, Para. 1 of the I Law").	Patent Law of the Peop	e-identified patent application for ole's Republic of China (hereafter application on its own initiative
2. [2	I	he applicant cla	simed prior	ity/priorities based	on the application(s):	
filed				October 15, 2003	, filed with	on
filed	wit	h	on		, filed with	on
filed	wit	h	on		, filed with	on
ŧ. [∑	. F	provision of Rul	e 51 of the	Implementing Reg	gulations of the Chines	are not in conformity with the e Patent Law. Istion of original international
		pplication as file				
] E	examination as	to substance	e was directed to the	he documents as speci	fied below:
	Ę] Specification	page(s)			text of international application ing Chinese national phase;
			page(s)			ext of the Annexes of International
			page(s)		Article 41 of Patent C	•
			page(s)			nts submitted under Rule 51, Para. g Regulations of the Patent Law.
		•	page(s)		directed to amendmen	ats submitted on
		Claims		**********	submitted when enter	text of international application ing Chinese national phase;
						text of amendments submitted atent Cooperation Treaty.
						ext of the Annexes of International
					Preliminary Report of	-
						nts submitted under Article 28 or
					Article 41 of Patent C	Congration Treaty

•			1 of the Ir	o amendments submitted under Rule 51, Para. nplementing Regulations of the Patent Law. o amendments submitted on
	Drawings	page(s)	when ente	o Chinese text of international application ring Chinese national phase;;
		page(s)	Prelimina	o Chinese text of the Annexes of International ry Report of patentability;
		page(s)	Article 41	of Patent Cooperation Treaty;
		page(s)	1 of the In	amendments submitted under Rule 51, Para. applementing Regulations of the Patent Law.
		page(s)	directed to	amendments submitted on
Ø		eference document examination proce		ction (the reference number will be used
No.	N	ımber or Title of F	eference	Date of Publication
				(or the filing date of conflicting application
1		KR2002-00796	59A	October 19, 2002
2				
	The specific	ation does not con	aply with Article 33 of	ura. 3 of the Patent Law. the Patent Law. Implementing Regulations of the Patent
\boxtimes	On the Claims:			
	Claim(s) 3	8	do not have novelt Patent Law.	y required by Article 22, Para. 2 of the
	Claim(s)		do not possess the in 3 of the Patent Law.	enventiveness required by Article 22, Para.
	Claim(s)		does/do not have ut Patent Law.	ility required by Article 22, Para.4 of the
	Claim(s)		-	under Article 25 of the Patent Law.
	Claim(s)		Law.	with Article 26, Para. 4 of the Patent
		(1, 24, 34-36)	- •	Article 31, Para. 1 of the Patent Law.
	Claim(s)			Article 33 of the Patent Law.
	Claim(s)		the Implementing Re	with the provisions of Rule 13, Para. 1 of egulations of the Patent Law.
	Claim(s)			with the provisions of Rule 2, Para. 1 of guilations of the Patent Law.

	ns 1, 2, 7, 8, 14-16	, do not comply with the provisions of Rule 20 of the
23-26, 32-36	•	Implementing Regulations of the Patent Law.
☐ Clain	n(s)	does/do not comply with the provisions of Rule 21 of the
_		Implementing Regulations of the Patent Law.
☐ Clain	1(8)	does/do not comply with the provisions of Rule 22 of the
		Implementing Regulations of the Patent Law.
☐ Clain	1(9)	does/do not comply with the provisions of Rule 23 of the
		Implementing Regulations of the Patent Law.
		ot comply with the provisions of Rule 43, Para. 1 of the
Impi	ementing Regulations of	the Patent Law.
For detail analy	sis of above conclusions	of the Action, see the Text of this Notification.
		e, the Examiner is of the opinion that:
		nts as directed in the Text of this Notification.
		ts in the response to the Notification and make amendments to
		as pointed out in the Text of the Notification. Otherwise, the
	vill not be issued a patent	
The applica	tion contains no allowa	ble invention, and therefore, if the applicant fails to submit
	ne reasons are not suffic	ient to prove that the application does have merits, it will be
rejected.		
7 The followings	Namid ka 401 (m. 1	
		deration by the applicant in making the response:
(1) Onder Artic	ie 37 of the Patent Law, 1	the applicant should respond to the office action within four (4)
		te Notification. If, without any justified reason, the time limit
		emed to have been withdrawn.
		should be in conformity with the provision of Article 33 of the
		d be in duplicate and the format of the substitution should be in
		n contained in "Examination Guidelines".
(3) The respons	e to the Nontication and	for revision of the application should be mailed to or handed
the Perestic	Reception Division of i	Patent Office, and the documents not mailed or handed over to
	n Division do not have le	-
(4) Without an a		nt and/or his agent(s) shall not interview with the Examiner in
mo I alent O	HIUG	
8. This Notification	on contains 2 magala) Tav	t and following attachments:
	forence, totaling <u>6</u> pages.	
	*** ****** ******************	

Text of the First Office Action

Application No.: 2004800159493

The present application relates to a nitride semiconductor light emitting device for

improving a light output and reliability. After examination, the following comments

are presented hereby:

1. The technical solution claimed in claim 38 does not possess novelty under Article

22, Para. 2 of the Chinese Patent Law. Reference document 1 (KR2002-0079659A)

discloses a nitride light emitting device, and it particularly discloses the following

technical features: "the light emitting device comprises: n-type electrode contact GaN

layer 22; an active layer 23 for emitting light formed above the n-type electrode

contact GaN layer 22; a p-type GaN layer 24 formed above the active layer; a n-type

electrode contact GaN layer 25 formed above the p-type GaN layer to have a super

lattice structure" (see Figure 3 and the abstract of the reference). It can be seen that,

D1 has disclosed all the technical features of the claim, both the technical solutions

are the same. And the technical solution disclosed in D1 and that claimed in the claim

38 belong to the same technical field, solve the same technical problem, and bring

about the same technical effect, thus the technical solution sought for protection in the

claim 38 does not possess novelty.

2. Independent claim 37 relates to a nitride semiconductor light emitting device.

Independent claims 1, 24, 34-36 also relate to a nitride semiconductor light emitting

device. The same or relevant technical feature contained in the two groups of claims is

"a first electrode contact layer", but this feature belongs to the conventional technical

means in the field. Thus the claims are impossible to contain the same or relevant

technical features that define a contribution which the invention makes over the prior

art, and obviously do not possess unity, and which fail to comply with the provisions

of Article 31, Para. 1 of the Chinese Patent Law.

3. The "cluster layer" in claims 1, 7, 8, 14, 15, 24, 25, 32-36 is unclear. "Cluster

layer" neither is the standard term in the art nor has been exactly defined in the description by the applicant. Therefore, the specific meaning of the "Cluster layer" is indefinite, it is unclear that by which substances the "Cluster layer" is formed and how the "Cluster layer" is formed. Thus claims 1, 7, 8, 14, 15, 24, 25, 32-36 fail to comply with the provisions of Rule 20, Para. 1 of the Implementing Regulations of the Chinese Patent Law.

4. The "SiN_a" in claims 8, 14, 15, 25, 32-26 is unclear. The expression manner thereof is not the standard expression in the art, the meaning and the specific value range for the subscript "a" are unclear. The applicant should state clearly the meaning thereof in the claims, thus claims 8, 14, 15, 25, 32-26 fail to comply with the provisions of Rule 20, Para. 1 of the Implementing Regulations of the Chinese Patent Law.

5. (omited)

6. The expression "(In_xGa_{1-x}N/In_yGa_{1-y}N super lattice)/n-GaN layered structure" in claim 16 is improper; the parentheses herein should be canceled. It can be written as "layered structure formed by In_xGa_{1-x}N/In_yGa_{1-y}N super lattice and n-GaN", in order to comply with the provisions of Rule 20, Para. 1 of the Implementing Regulations of the Chinese Patent Law.

- 7. The parentheses appeared in claim 23 should be deleted, and the claim can be expressed as "wherein 0<x<0.1" instead, in order to comply with the provisions of Rule 20, Para. 1 of the Implementing Regulations of the Chinese Patent Law.
- 8. The "p-nitride" in claim 33 should be amended into "p-type nitride", in order to comply-with the provisions of Rule 20, Para 1 of the Implementing Regulations of the Chinese Patent Law.

Based on the above reasons, the present application cannot be granted according to

the current text, the applicant should make amendment to the application documents in order to overcome the defects therein, and make arguments for the inventiveness and novelty of the amended claims over the reference document. Any amendment to the application documents should comply with the provisions of Article 33 of the Chinese Patent Law, and it cannot go beyond the scope of the original claims and description. In the meantime, please note that, according to the provisions of Article 38 of the Chinese Patent Law, if the amended text still possesses the defects stated in Rule 53 of the Implementing Regulations of the Chinese Patent Law as pointed out in the Office Action, the present application will be rejected.

Examiner: CHEN LONG

Code: 95A7